

DOCKET NO. 99-039



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IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicants: : Sheldon Aronowitz, Valeriy Sukharev, John Haywood, James P. Kimball,
Helmut Puchner, Ravindra Manohar Kapre, and Nicholas Eib

Appl. No. : 09/464,297

Filed: : December 15, 1999

Title : PROCESS FOR ETCHING A CONTROLLABLE THICKNESS OF
OXIDE ON AN INTEGRATED CIRCUIT STRUCTURE ON A
SEMICONDUCTOR SUBSTRATE USING NITROGEN PLASMA AND
AN RF BIAS APPLIED TO THE SUBSTRATE

Grp./ A.U. : 1765

Examiner : Charlotte A. Brown

Docket No. : 99-039

CERTIFICATE OF MAILING	
I hereby certify that this correspondence is being deposited with the United States Postal Service as first class mail in an envelope addressed to: Assistant Commissioner for Patents, Washington, D.C. 20231	
on	<u>August 14, 2001</u>
(Date of Deposit)	
John P. Taylor, Reg. No. 22,369	
<u>John P. Taylor</u>	
Signature	
	<u>August 14, 2001</u>
Date of Signature	

AMENDMENT

Honorable Commissioner for Patents
Washington, D.C. 20231

Date: August 14, 2001

Sir:

In response to the Office Action mailed June 5, 2001, please amend the
application as follows: